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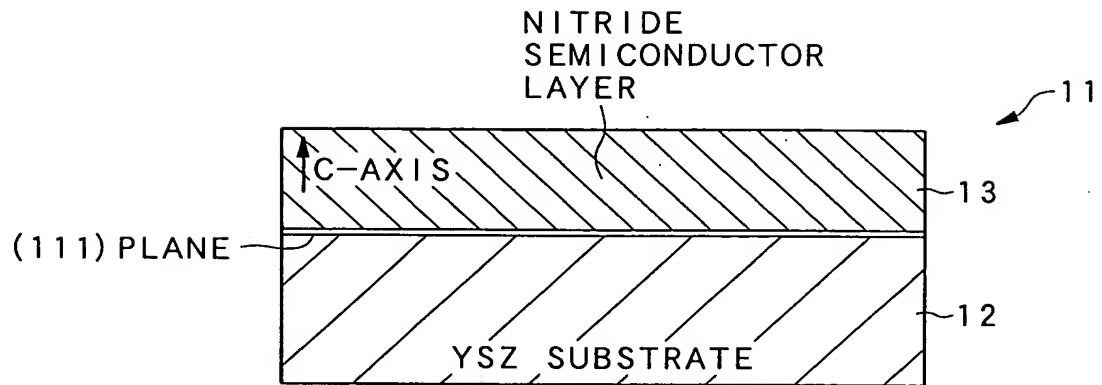


FIG. 1

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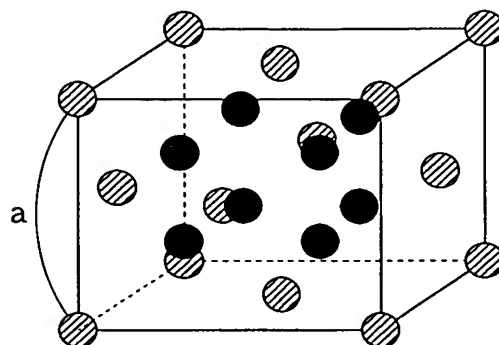


FIG. 2A

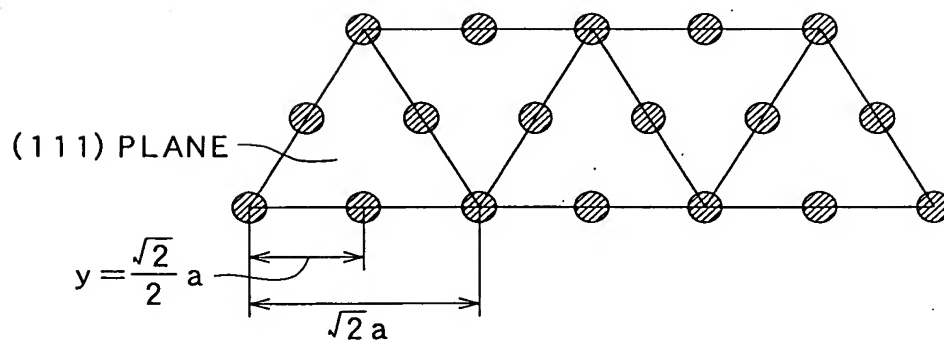


FIG. 2B

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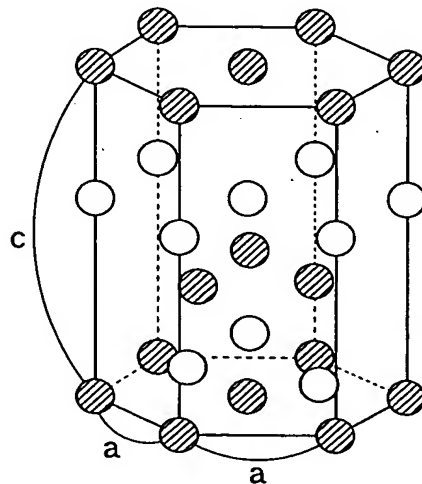


FIG. 3A

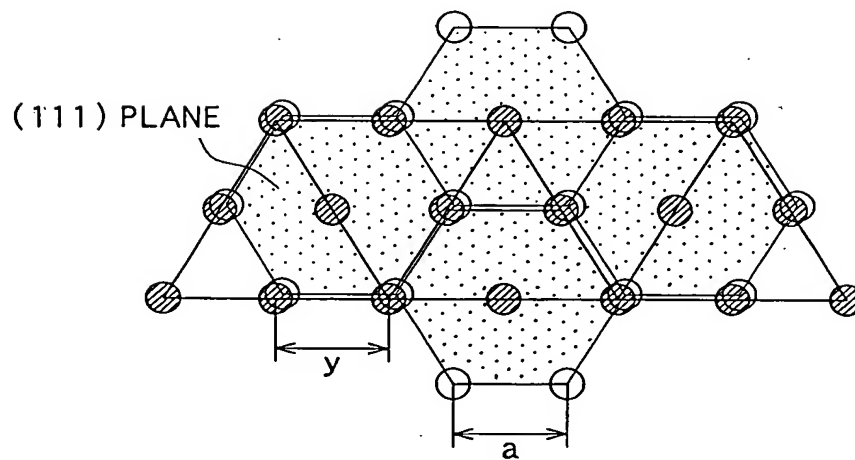


FIG. 3B

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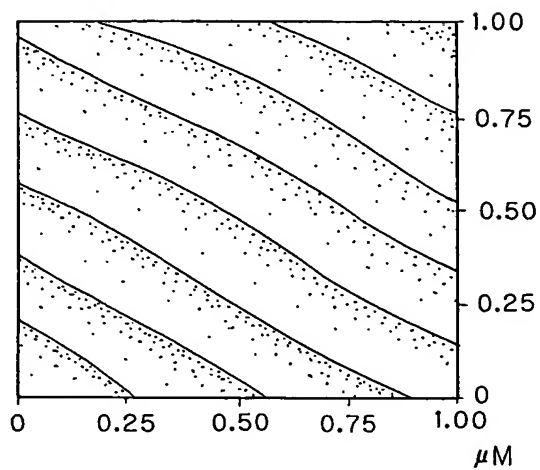


FIG. 4

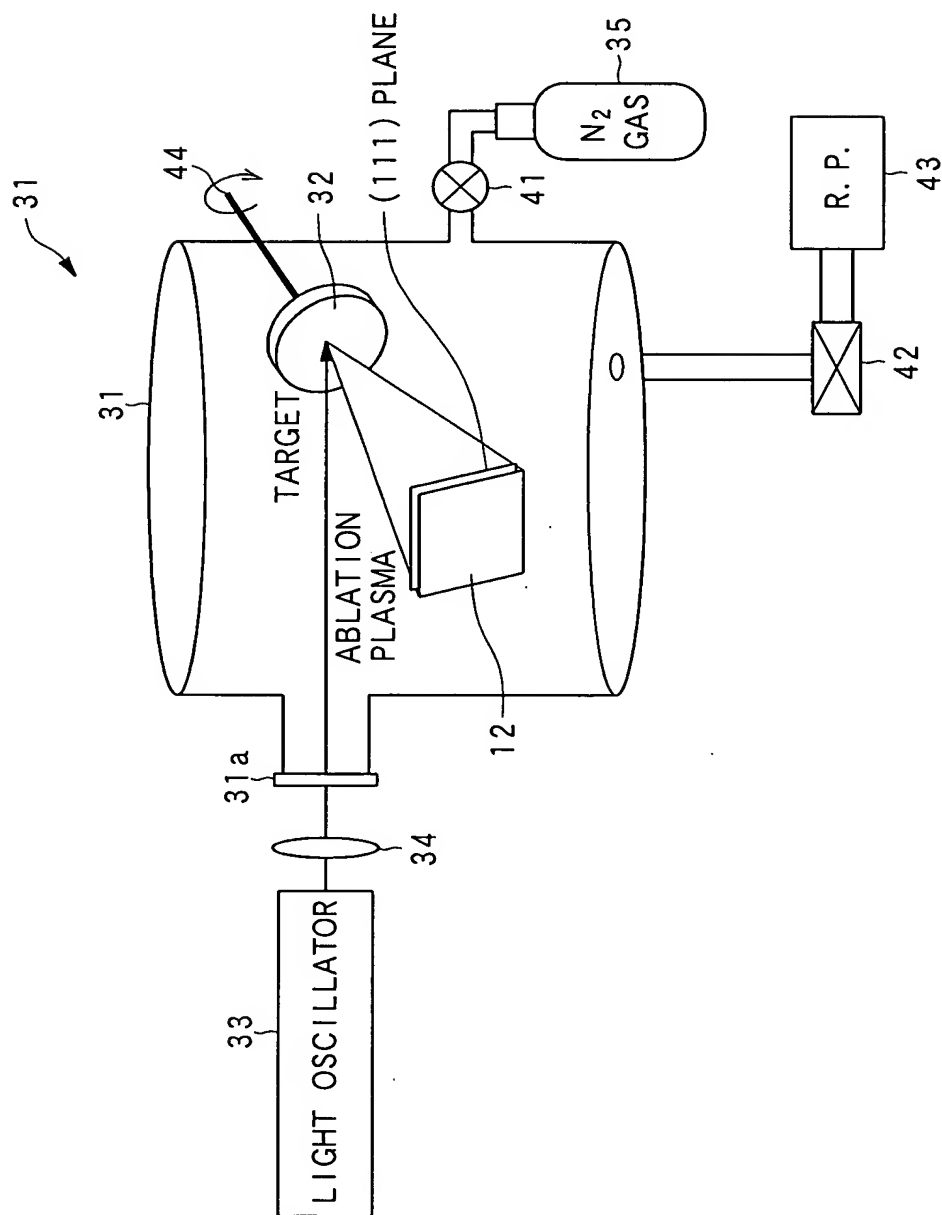
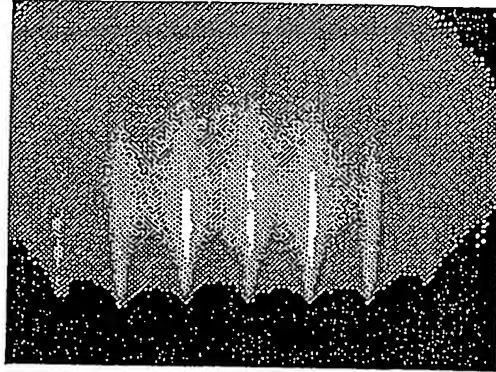


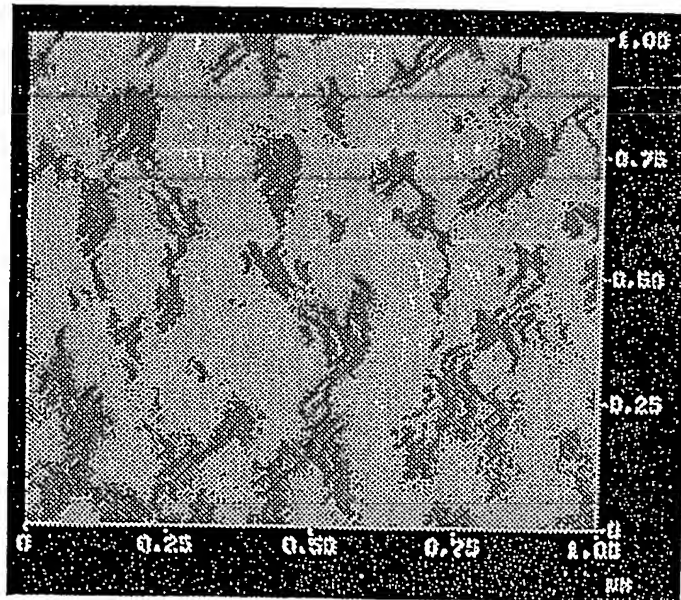
FIG. 5

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F I G. 6



F I G. 7

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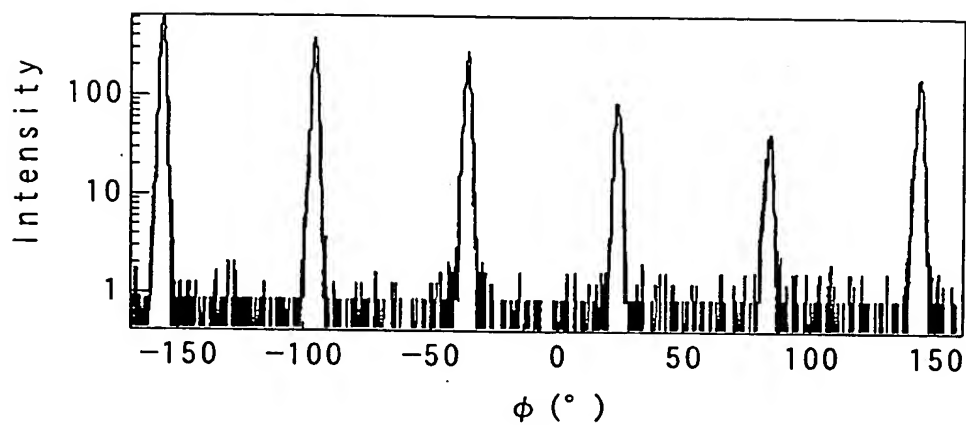


FIG. 8A

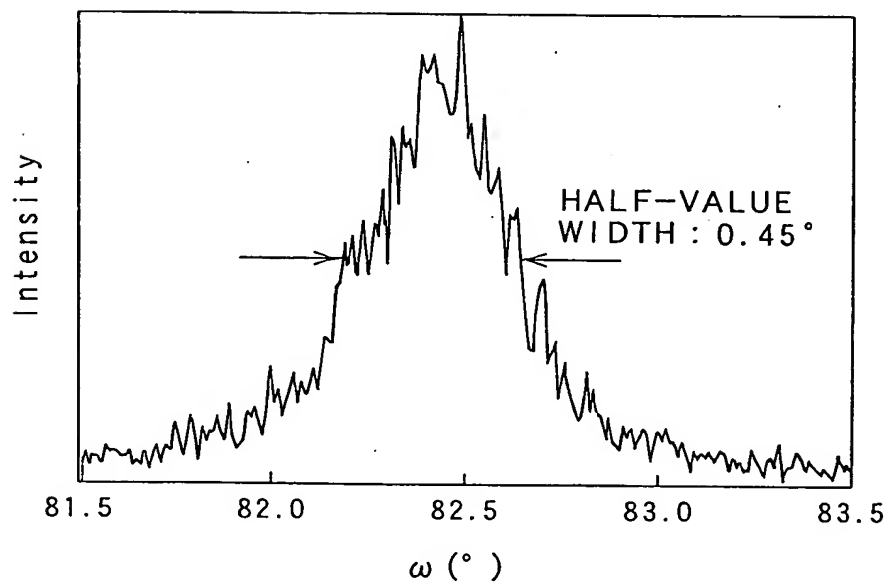


FIG. 8B

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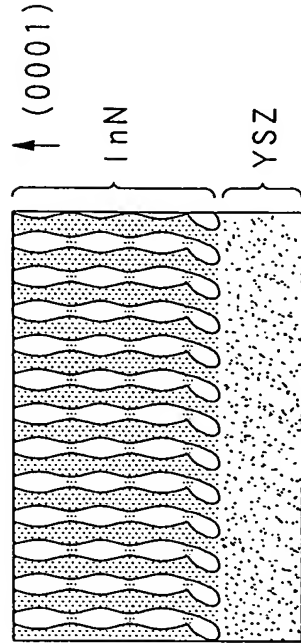


FIG. 9B

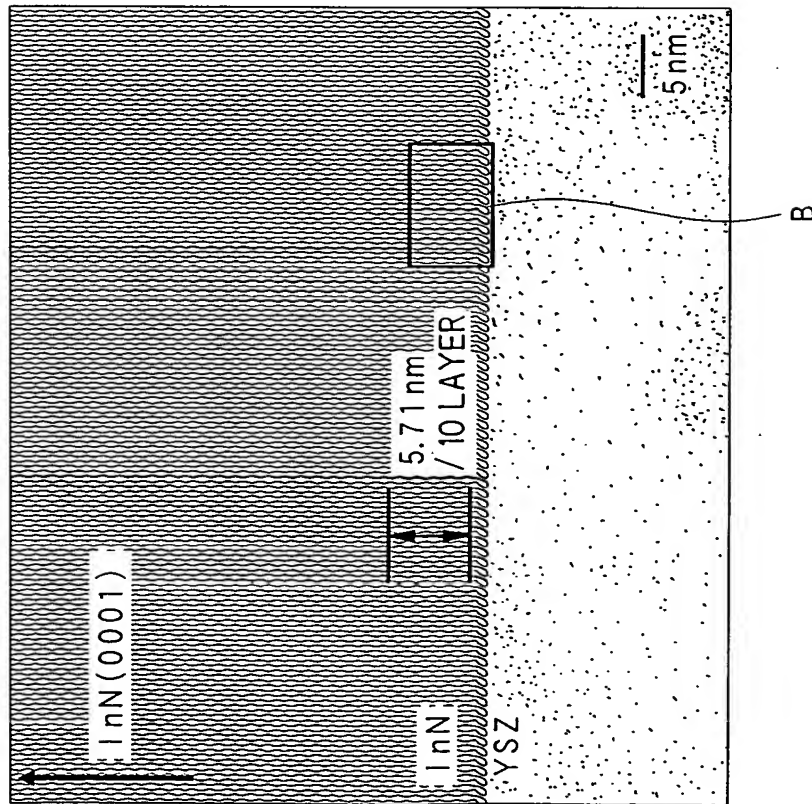


FIG. 9A

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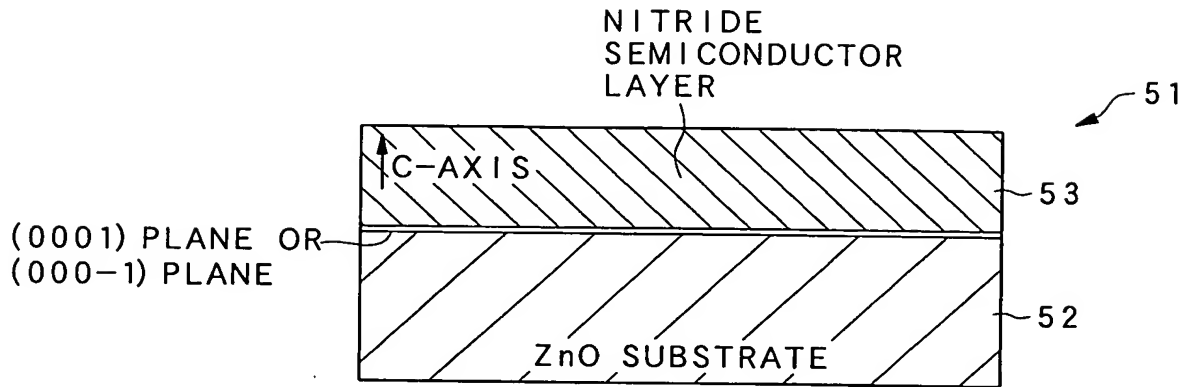


FIG.10

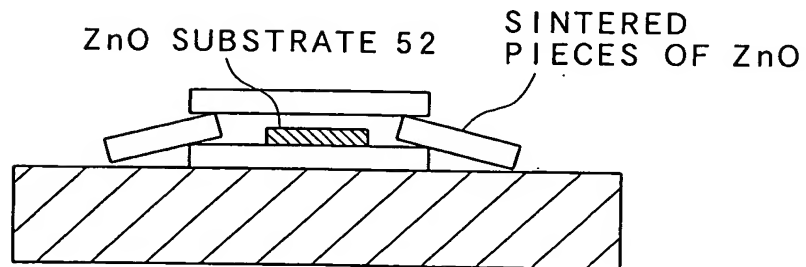
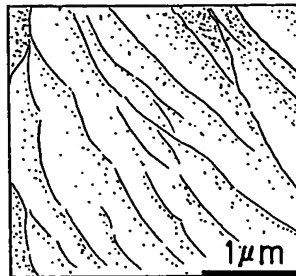


FIG.11

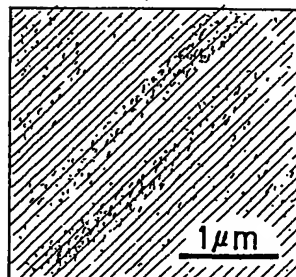
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FIG.12A



1150 °C 6.5h

FIG.12B



1150 °C 3.5h

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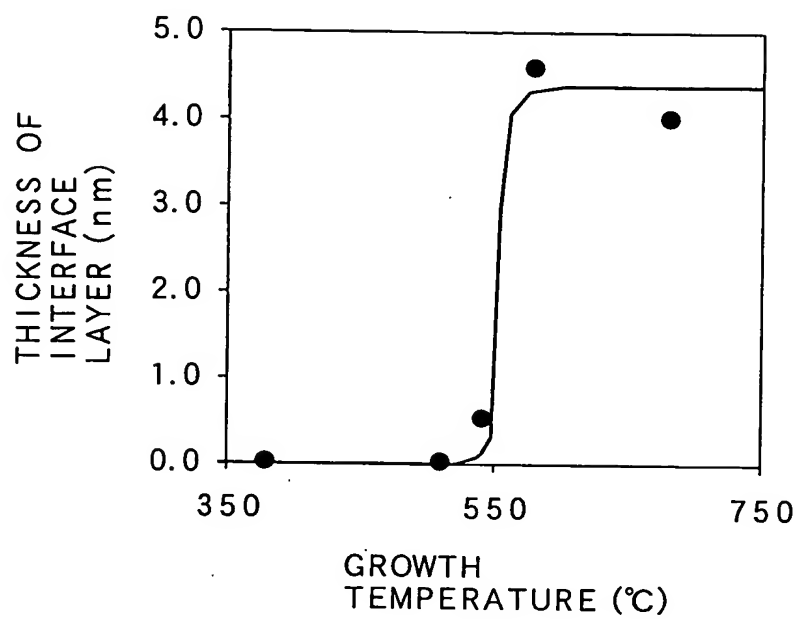
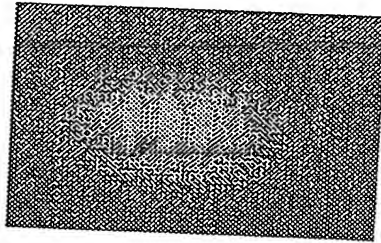


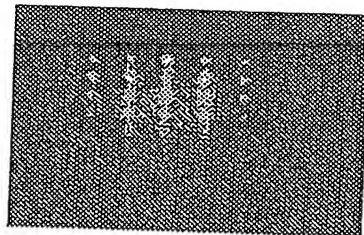
FIG.13

Inventor(s): Fujioka et al.
NITRIDE SEMICONDUCTOR DEVICE AND METHOD FOR
PREPARATION THEREOF
Filed January 6, 2006; Atty. Docket No. 113184-114

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F I G. 1 4 A



F I G. 1 4 B

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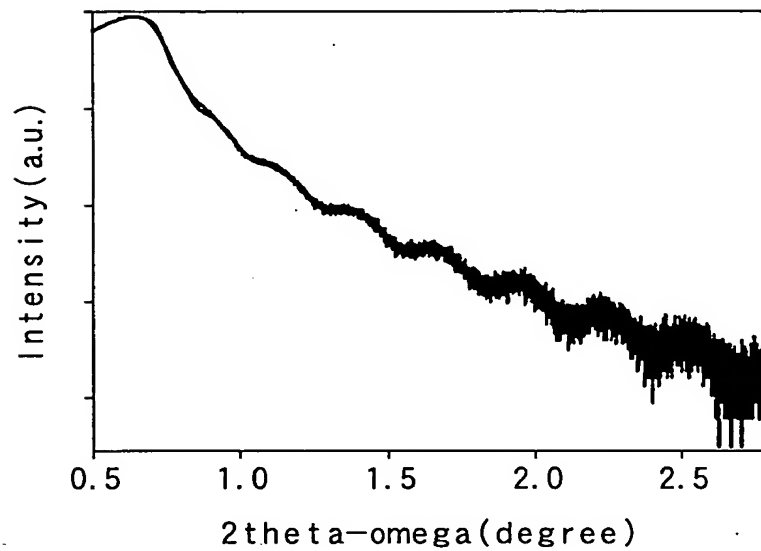


FIG.15

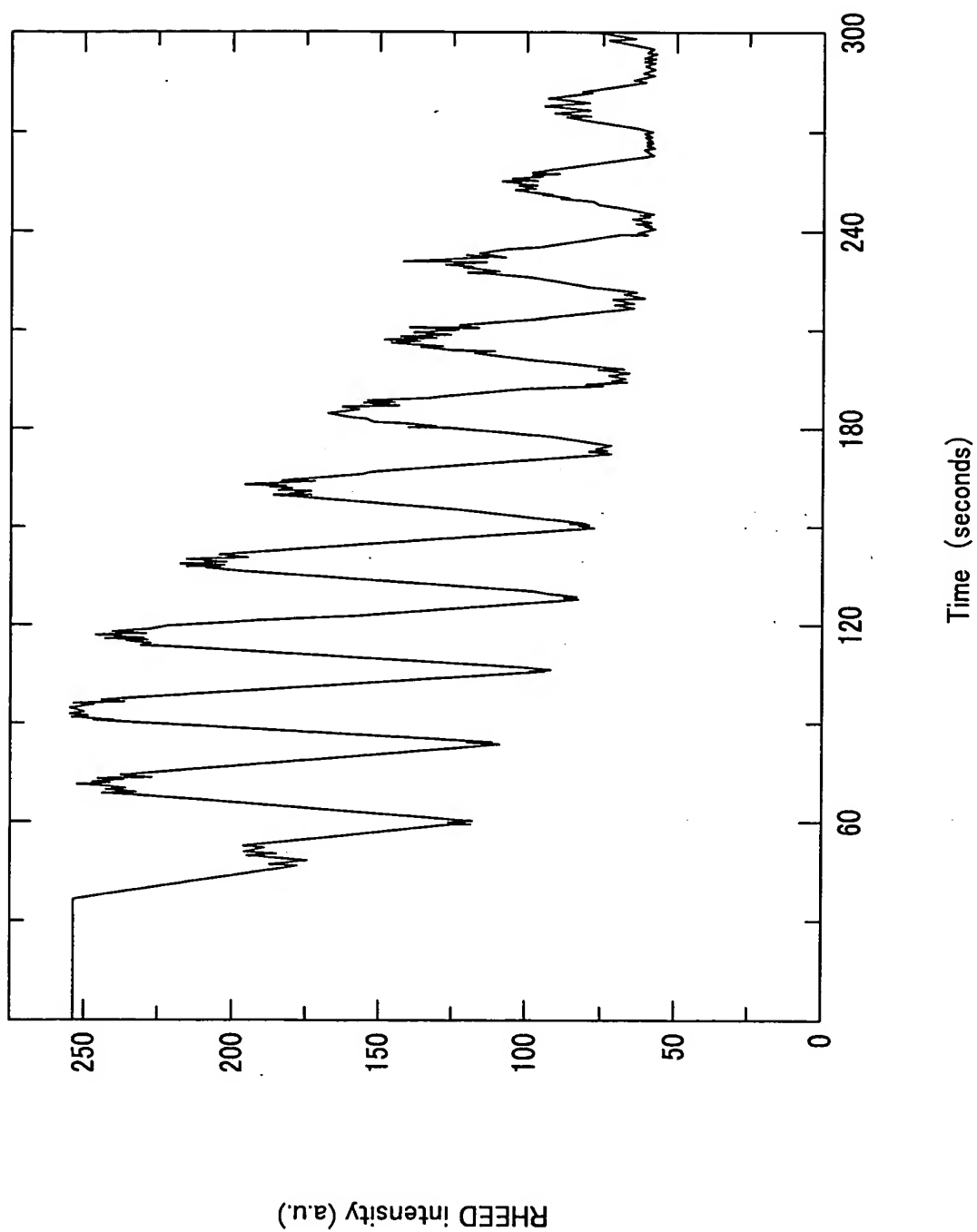


FIG. 16